

**SECTION I. (AMENDMENTS TO THE CLAIMS)**

A listing of claims 1-33 of the present application, with markings showing amendments made herein, is provided below:

Claims 1-23. (Canceled)

Claim 24 (Previously presented) An electrical contact to a region of a silicon-containing substrate comprising a substrate having an exposed region of a silicon-containing semiconductor material; and a first layer of Ni monosilicide, wherein said substrate and said first layer are separated by a Si-Ge interlayer and said first layer of Ni monosilicide comprises at least one additive selected from the group consisting of C, Al, Sc, Ti, V, Cr, Mn, Fe, Co, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir, Pt, Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Tb and Lu.

Claim 25 (Previously presented) The electrical contact of Claim 24 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).

Claims 26-27 (Canceled)

Claim 28 (Previously presented) The electrical contact of Claim 24 wherein said substrate is doped.

Claim 29 (Previously presented) The electrical contact of Claim 24 wherein said substrate includes a p<sup>+</sup> silicon area.

Claim 30 (Previously presented) The electrical contact of Claim 24 wherein said substrate includes an n<sup>+</sup> silicon area.

Claim 31 (Previously presented) The electrical contact of Claim 24 wherein said at least one additive is C, Al, Sc, Ti, V, Cr, Mn, Fe, Co, Cu, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir or Pt.

Claim 32 (Currently amended) ~~The~~ An electrical contact of Claim 31 wherein said to a region of a silicon-containing substrate comprising a substrate having an exposed region of a silicon-containing semiconductor material; and a first layer of Ni monosilicide, wherein said substrate and said first layer are separated by a Si-Ge interlayer and said first layer of Ni monosilicide comprises at least one additive that is Ti, V, Cr, Nb, Rh, Ta, Re or Ir.

Claim 33 (New) An electrical contact to a region of a silicon-containing substrate comprising a substrate having an exposed region of a silicon-containing semiconductor material; and a first layer of Ni monosilicide, wherein said substrate and said first layer are separated by a Si-Ge interlayer and said first layer of Ni monosilicide comprises at least one additive selected from the group consisting of C, Al, Sc, Ti, V, Cr, Mn, Fe, Co, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir, Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Tb and Lu.